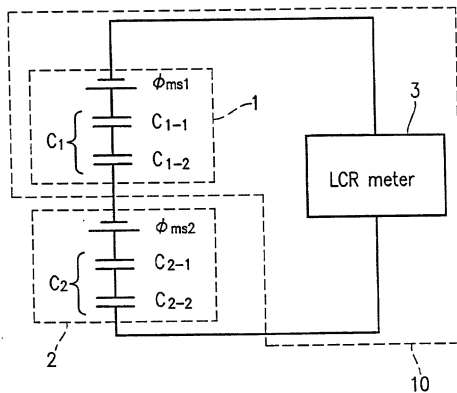


01R00422

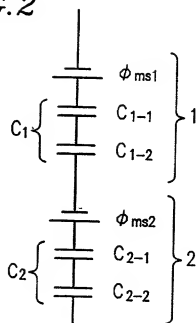
FIG. 1



1000222-120601

01R00422

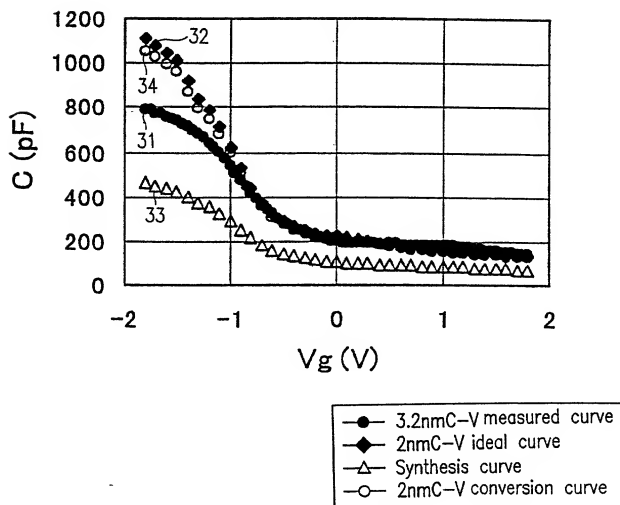
*FIG. 2*



1003253-10001

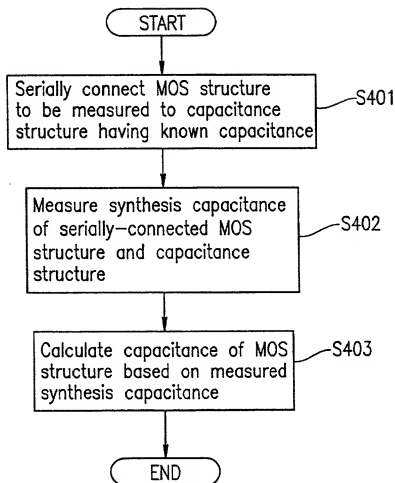
FIG. 3

NMOS C-V Characteristics



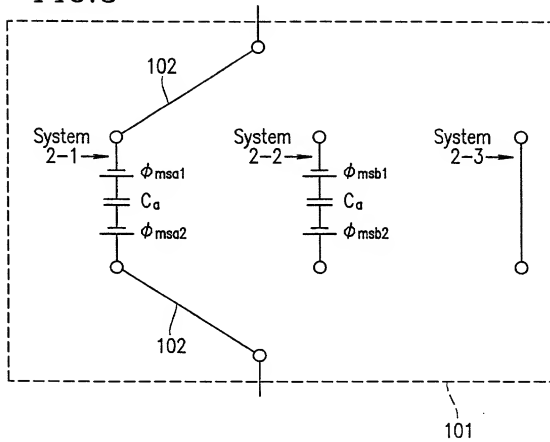
01R00422

*FIG. 4*



01R00422

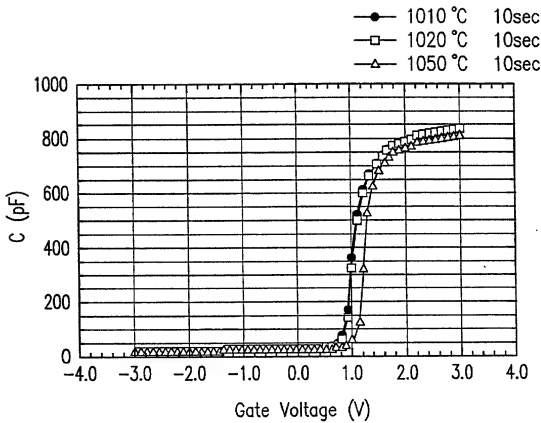
FIG. 5



01R00422

**FIG. 6**

PMOS C-V Characteristics



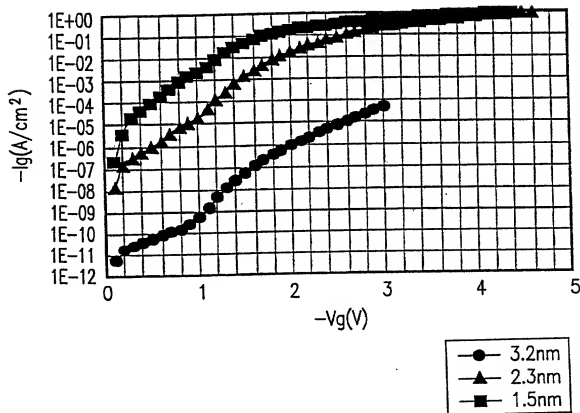
Active Area:  $9\text{E}-4\text{cm}^2$   
w/o Well Imp.  
Gate SiON: NO/ $\text{N}_2$

poly Si: 200nm  
P+Imp.:  $\text{BF}_2$

01R00422

FIG. 7

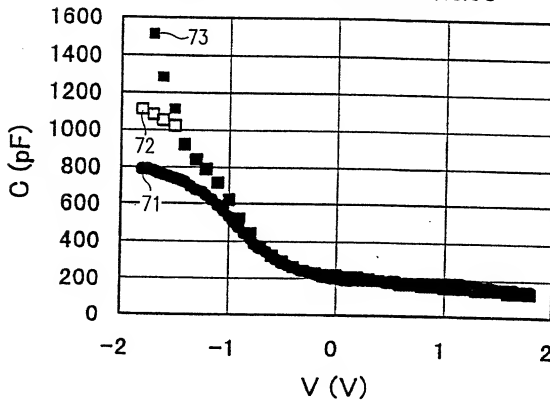
NMOS I-V Characteristics



01R00422

FIG. 8

NMOS C-V Characteristics

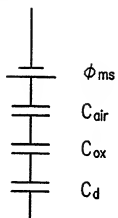


- 3.2nmC-V measured curve
- 2nmC-V ideal curve
- 2nmC-V measured curve

1000356.120604  
1000356.120604

01R00422

*FIG. 9*



1000222.120604